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Ion irradiation and semiconductor detector characterization at the Centro Nacional de Aceleradores [MONDAY]

Monday 21 November 2016 11:45 (20 minutes)

The National Accelerator Center (CNA) is a user's facility dedicated to multidisciplinary applications of particle accelerators. In this talk, the infrastructure available at CNA for Ion Irradiation and Characterization of Materials, based on a 3 MV tandem accelerator and a compact cyclotron for 18 MeV protons, will be briefly described. Recent activities carried out at CNA with potential interest for RD50 participants will be presented. The examples include the strain response of proton-irradiated Fiber Bragg Gratings, soft errors produced in SRAM memories and applications of the Ion Beam Induced Current technique to study the transport properties of ion induced damaged Si and SiC diodes and the charge collection efficiency of silicon-3D and Low Gain Avalanche Detectors.

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